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The invention relates to gas-sensitive devices, particularly to the semiconducting sensors of toxic gases.

Summary of the invention consists in that the thin film semiconducting sensor of toxic gases contains an isolated substrate, onto which is applied a gas-sensitive stratum of chalcogenic semiconductor, containing tellurium and its alloys. On the sensitive stratum there are applied two electrodes, placed longitudinal or transversal.

The result of the invention consists in the creation of a fast sensor, functioning at the room temperature.